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978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS  
 Scaling: Materials Research Society Symposium Proceedings: Volume 1252  
 Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel,  
 Heiji Watanabe, Iain Thayne and Prashant Majhi

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